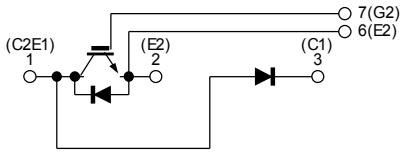
日本インター株式会社
Nihon Inter Electronics Corporation

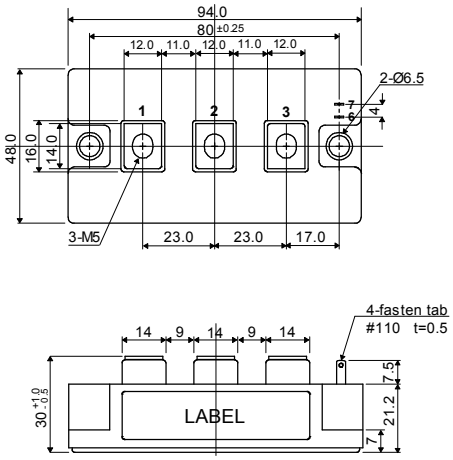
ＩＧＢＴ Module
１５０Ａ／６００Ｖ

ＰＲＦＭＢ１５０Ｅ６

□ 回路図 ： *CIRCUIT*



□ 外形寸法図 ： *OUTLINE DRAWING*



Dimension: [mm]

□ 最大定格 ： *MAXIMUM RATINGS* (at Tc=25℃ unless otherwise specified)

Item		Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage		VCES	６００	V
ゲート・エミッタ間電圧 Gate-Emitter Voltage		VGES	±２０	V
コレクタ電流 Collector Current	DC	IC	１５０	A
	1ms	ICP	３００	
コレクタ損失 Collector Power Dissipation		PC	５６０	W
接合温度 Junction Temperature Range		Tj	－４０～＋１５０	℃
保存温度 Storage Temperature Range		Tstg	－４０～＋１２５	℃
絶縁耐圧 (Terminal to Base AC, 1minute) Isolation Voltage		VISO	２,５００	V(RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink	Ftor	３（３０.６）	N・m (kgf・cm)
	Busbar to Main Terminal		２（２０.４）	

□ 電気的特性 ： *ELECTRICAL CHARACTERISTICS* (at Tj=25℃ unless otherwise specified)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current		ICES	VCE= 600V, VGE= 0V	－	－	１.０	mA
ゲート漏れ電流 Gate-Emitter Leakage Current		IGES	VGE= ±20V, VCE= 0V	－	－	１.０	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage		VCE(sat)	IC= 150A, VGE= 15V	－	２.１	２.６	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage		VGE(th)	VCE= 5V, IC= 150mA	４.０	－	８.０	V
入力容量 Input Capacitance		Cies	VCE= 10V, VGE= 0V, f= 1MHz	－	７,５００	－	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	tr	VCC= 300V RL= 2.0Ω RG= 5.1Ω VGE= ±15V	－	０.１５	０.３０	μs
	ターンオン時間 Turn-on Time	ton		－	０.２５	０.４０	
	下降時間 Fall Time	tf		－	０.１０	０.３５	
	ターンオフ時間 Turn-off Time	toff		－	０.３５	０.７０	

□ フリーホイーリングダイオードの特性： *FREE WHEELING DIODE RATINGS* (at Tc=25℃) & *CHARACTERISTICS* (at Tj=25℃)

Item		Symbol	Rated Value	Unit
順電流 Forward Current	DC	IF	１５０	A
	1ms	IFM	３００	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
順電圧 Peak Forward Voltage	VF	IF= 150A, VGE= 0V	－	１.９	２.４	V
逆回復時間 Reverse Recovery Time	trr	IF= 150A, VGE= -10V di/dt= 300A/μs	－	０.１５	０.２５	μs

□ 熱的特性 ： *THERMAL CHARACTERISTICS*

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	Rth(j-c)	Junction to Case (Tcチップ直下での測定点)	－	－	０.２２	℃／W
	Diode			－	－	０.４５	

Fig.1- Output Characteristics (Typical)

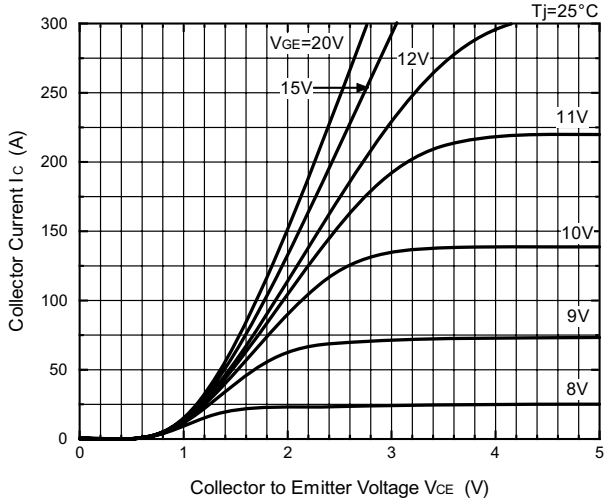


Fig.2- Output Characteristics (Typical)

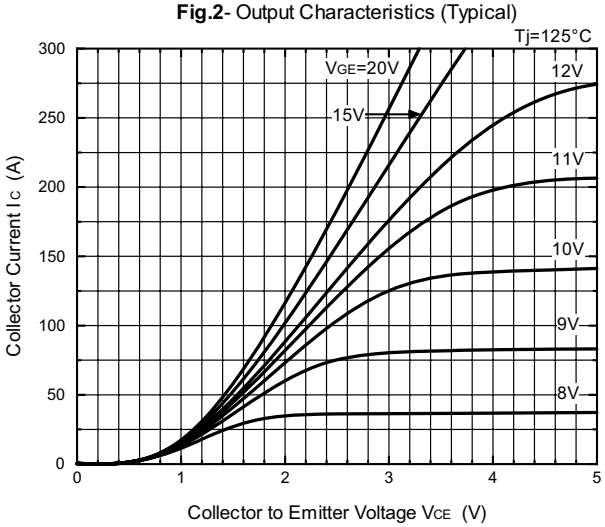


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

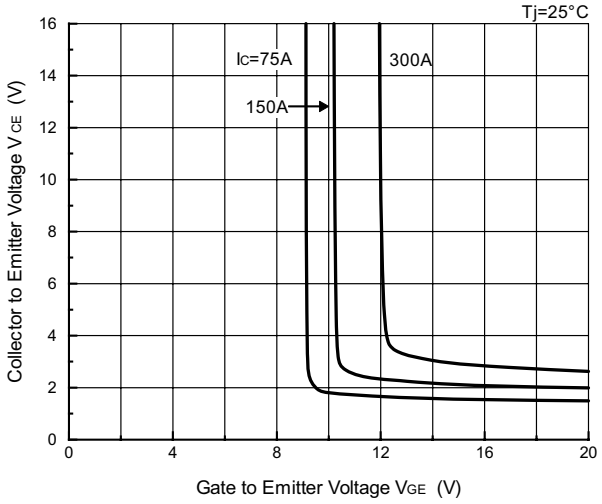


Fig.4- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

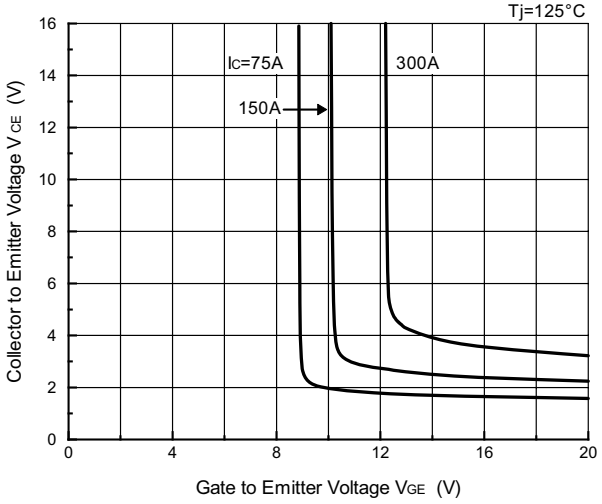


Fig.5- Gate Charge vs. Collector to Emitter Voltage (Typical)

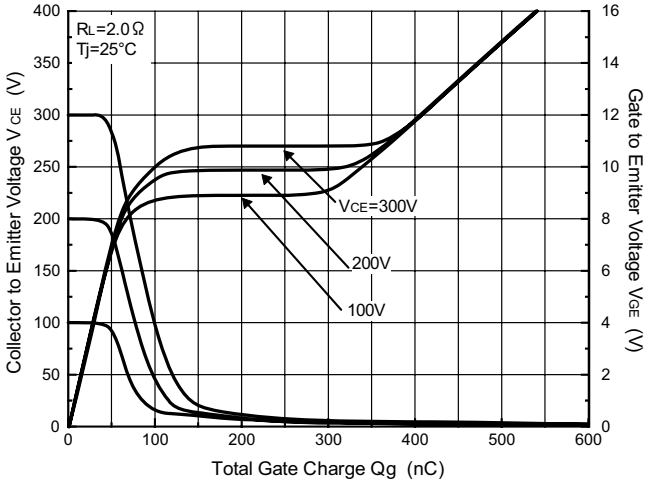


Fig.6- Capacitance vs. Collector to Emitter Voltage (Typical)

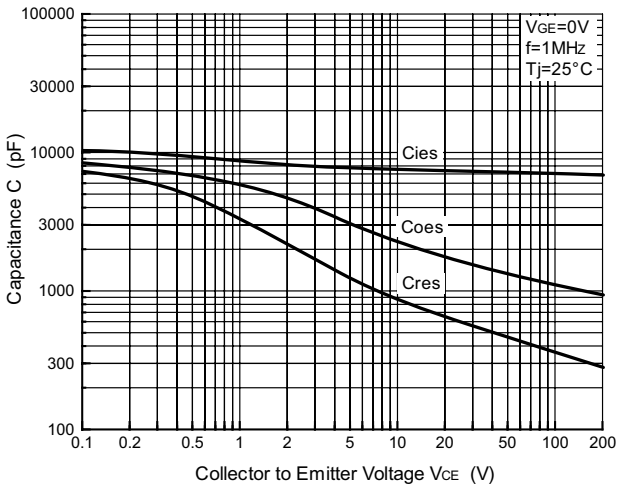


Fig.7- Collector Current vs. Switching Time (Typical)

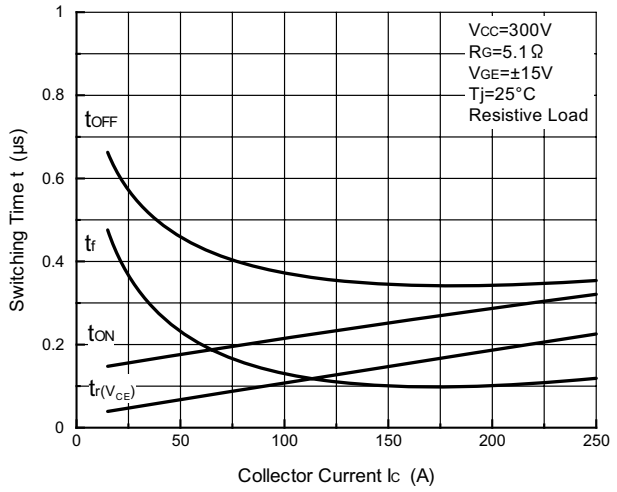


Fig.8- Series Gate Impedance vs. Switching Time (Typical)

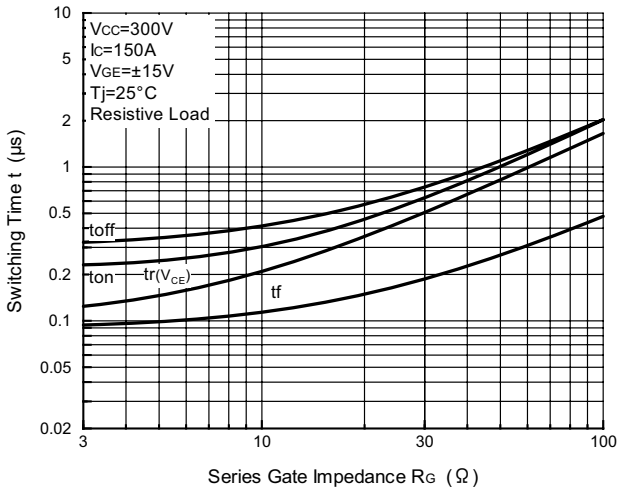


Fig.9- Collector Current vs. Switching Time

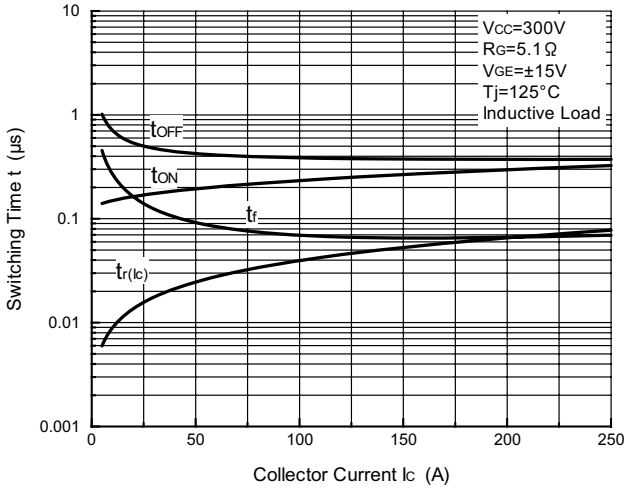


Fig.10- Series Gate Impedance vs. Switching Time

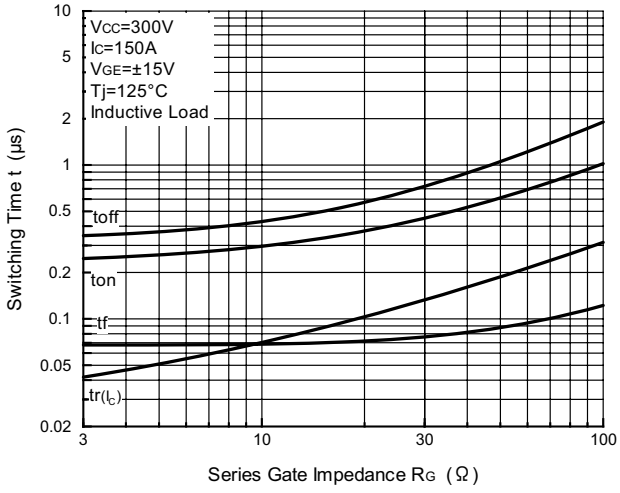


Fig.11- Collector Current vs. Switching Loss

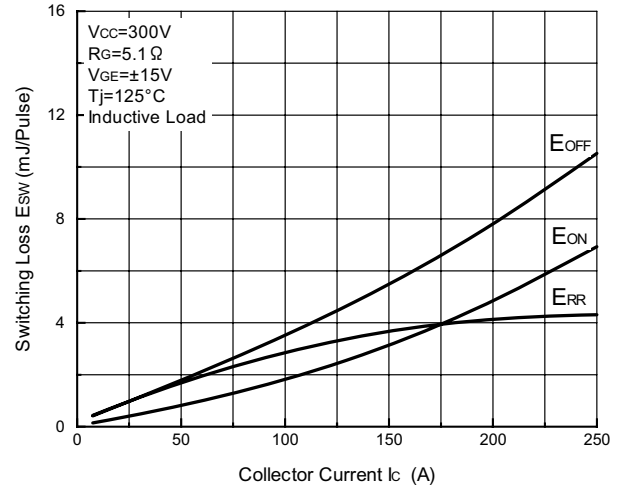


Fig.12- Series Gate Impedance vs. Switching Loss

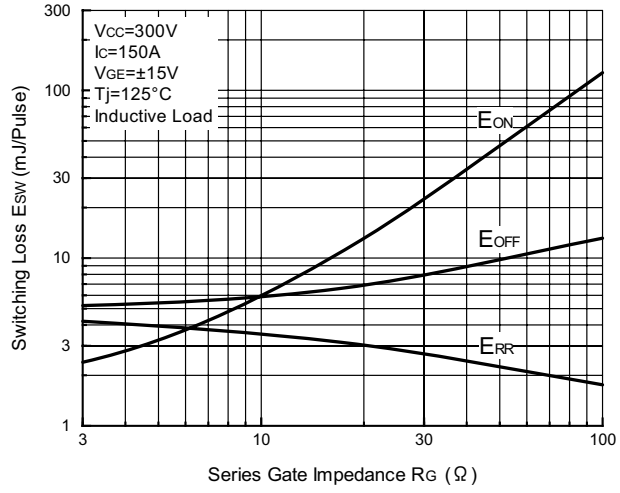


Fig.13- Forward Characteristics of Free Wheeling Diode (Typical)

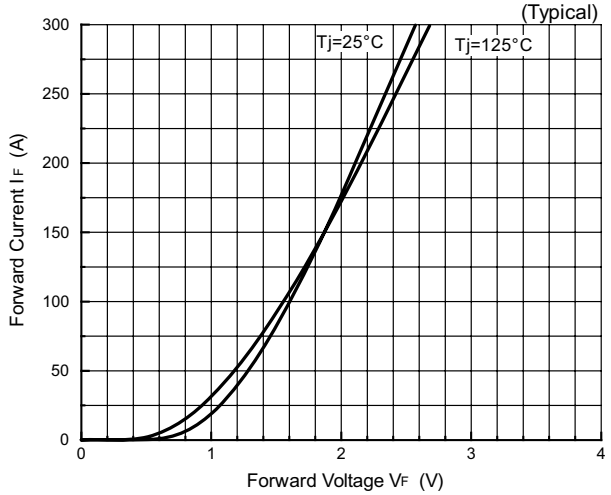


Fig.14- Reverse Recovery Characteristics (Typical)

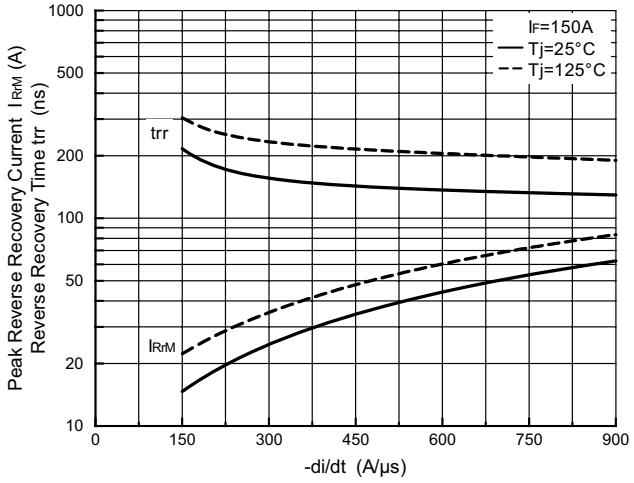


Fig.15- Reverse Bias Safe Operating Area

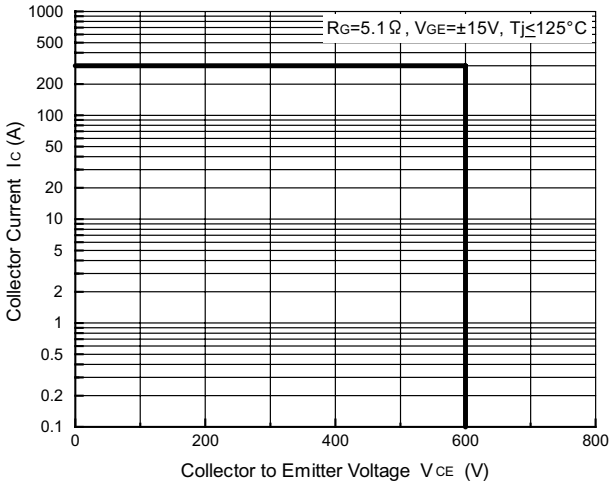


Fig.16- Transient Thermal Impedance